

Self-Protected High Side Driver with Temperature and Current Limit

NCV8450, NCV8450A

The NCV8450/A is a fully protected High–Side Smart Discrete device with a typical $R_{DS(on)}$ of 1.0 Ω and an internal current limit of 0.8 A typical. The device can switch a wide variety of resistive, inductive, and capacitive loads.

Features

- Short Circuit Protection
- Thermal Shutdown with Automatic Restart
- Overvoltage Protection
- Integrated Clamp for Inductive Switching
- Loss of Ground Protection
- ESD Protection
- Slew Rate Control for Low EMI
- Very Low Standby Current
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Automotive
- Industrial

PRODUCT SUMMARY

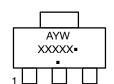
Symbol	Characteristics	Value	Unit
V _{IN_CL}	Overvoltage Protection	54	V
V _{D(on)}	Operation Voltage	4.5 – 45	V
R _{on}	On-State Resistance	1.0	Ω

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MARKING DIAGRAM



CASE 318E



XXXXX = V8450 or 8450A A = Assembly Location

Y = Year
W = Work Week
Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.

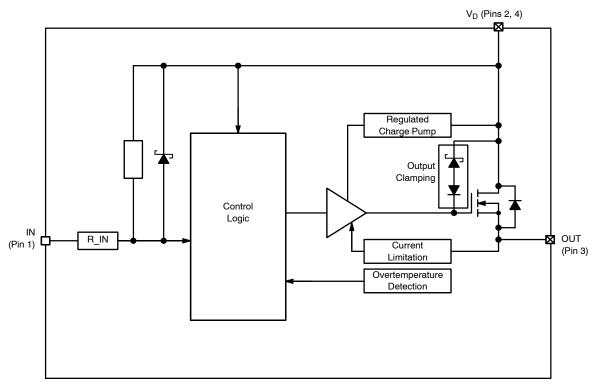


Figure 1. Block Diagram

PACKAGE PIN DESCRIPTION

Pin #	Symbol	Description
1	IN	Control Input, Active Low
2	V_{D}	Supply Voltage
3	OUT	Output
4	V_{D}	Supply Voltage

MAXIMUM RATINGS

		Value		
Rating	Symbol	Min	Max	Unit
DC Supply Voltage (Note 1)	V _D	-16	45	V
Load Dump Protection (RI = 2 Ω , t_d = 400 ms, V_{IN} = 0, 10 V, I_L = 150 mA, V_{bb} = 13.5 V)	V _{Loaddump}		85	V
Input Current	I _{in}	-15	15	mA
Output Current (Note 1)	I _{out}		Internally Limited	Α
Total Power Dissipation @ T _A = 25°C (Note 2) @ T _A = 25°C (Note 3)	P _D		1.13 1.60	W
Electrostatic Discharge (Note 4) (Human Body Model (HBM) 100 pF/1500 Ω) Input All other			1 5	kV
Single Pulse Inductive Load Switching Energy (Note 4) ($V_{DD}=13.5~V,~I=465~mApk,~L=200~mH,~T_{JStart}=150^{\circ}C$)	E _{AS}		29	mJ
Operating Junction Temperature	TJ	-40	+150	°C
Storage Temperature	T _{storage}	-55	+150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Reverse Output current has to be limited by the load to stay within absolute maximum ratings and thermal performance.

- 2. Minimum Pad.
- 1 in square pad size, FR-4, 1 oz Cu.
 Not subjected to production testing.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max Value	Unit
Thermal Resistance (Note 5) Junction-to-Ambient (Note 2) Junction-to-Ambient (Note 3)	$R_{ heta JA} \ R_{ heta JA}$	110 78.3	K/W

5. Not subjected to production testing.

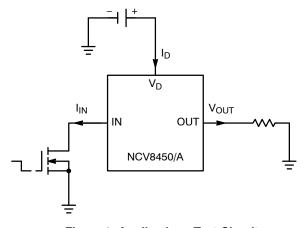


Figure 2. Applications Test Circuit

ELECTRICAL CHARACTERISTICS (6 \leq V_D \leq 45 V; $-40^{\circ}C$ <T_J < 150 $^{\circ}C$ unless otherwise specified)

				Value		
Rating	Symbol	Conditions	Min	Тур	Max	Unit
OUTPUT CHARACTERISTICS						
Operating Supply Voltage	V _{SUPPLY}		4.5	-	45	V
On Resistance (Pin 1 Connected to GND)	R _{ON}	$T_J = 25^{\circ}\text{C}$, $I_{OUT} = 150$ mA, $V_D = 7$ V $- 45$ V $T_J = 150^{\circ}\text{C}$, $I_{OUT} = 150$ mA, $V_D = 7$ V $- 45$ V (Note 6) $T_J = 25^{\circ}\text{C}$, $I_{OUT} = 150$ mA, $V_D = 6$ V		1.0	2 3	Ω
Standby Current (Pin 1 Open)	I _D	$V_D \le 20 \text{ V}$		0.6	2.1	μΑ
Glandby Guiterit (Firit Toperi)	טי	$V_D = 20 \text{ V}$ $V_D > 20 \text{ V}$		0.0	100	μΛ
INPUT CHARACTERISTICS						
Input Current – Off State	I _{IN_OFF}	$V_{OUT} \le 0.1 \text{ V, } R_L = 270 \ \Omega, \ T_J = 25^{\circ}\text{C} \ V_{OUT} \le 0.1 \text{V, } R_L = 270 \ \Omega, \ T_J = 150^{\circ}\text{C} \ (\text{Note 6})$	-50 -40			μΑ
Input Current – On State (Pin 1 Grounded)	I _{IN_ON}			1.5	3	mA
Input Resistance (Note 6)	R _{IN}			1		kΩ
SWITCHING CHARACTERISTICS	3					
Turn-On Time (Note 7) (V _{IN} = V _D to 0 V) to 90% V _{OUT}	t _{ON}	$R_L = 270 \ \Omega \ (Note 6)$ $V_D = 13.5 \ V, \ R_L = 270 \ \Omega, \ T_J = 25^{\circ}C$		30	125 100	μs
Turn-Off Time (Note 7) $(V_{IN} = 0 \text{ V to } V_D)$ to 10% V_{OUT}	t _{OFF}	R_L = 270 Ω (Note 6) V_D = 13.5 V, R_L = 270 Ω , T_J = 25°C		60	175 150	μS
Slew Rate On (Note 7) (V _{IN} = V _D to 0V) 10% to 30% V _{OUT}	dV/dt _{ON}	R_L = 270 Ω (Note 6) V_D = 13.5 V, R_L = 270 Ω , T_J = 25°C		0.7	4 4	V/μs
Slew Rate Off (Note 7) (V _{IN} = 0 V to V _D) 70% to 40% V _{OUT}	dV/dt _{OFF}	R_L = 270 Ω (Note 6) V_D = 13.5 V, R_L = 270 Ω , T_J = 25°C		0.9	4 4	V/μs
OUTPUT DIODE CHARACTERIS	TICS (Note 6)					
Drain-Source Diode Voltage	V _F	I _{OUT} = -0.2 A		0.6		V
Continuous Reverse Drain Current	I _S	T _J = 25°C			0.2	Α
PROTECTION FUNCTIONS (Note	e 8)					
Temperature Shutdown (Note 6)	T _{SD}		150	175	_	°C
Temperature Shutdown Hysteresis (Note 6)	T _{SD_HYST}			5		°C
Output Current Limit	I _{LIM}	$T_J = -40^{\circ}\text{C}, \ V_D = 13.5 \text{ V}, \ t_m = 100 \ \mu\text{s} \ \text{(Note 6)} \ T_J = 25 \ ^{\circ}\text{C}, \ V_D = 13.5 \ \text{V}, \ t_m = 100 \ \mu\text{s} \ \text{(Note 6)} \ T_J = 150 \ ^{\circ}\text{C}, \ V_D = 13.5 \ \text{V}, \ t_m = 100 \ \mu\text{s} \ \text{(Note 6)} \ (Not$	0.5	0.8	1.5	A
Output Clamp Voltage (Inductive Load Switch Off) At V _{OUT} = V _D - V _{CLAMP}	V _{CLAMP}	I _{OUT} = 4 mA	45	52		V
Overvoltage Protection	V _{IN_CL}	I _{CLAMP} = 4 mA	50	54		V

^{6.} Not subjected to production testing
7. Only valid with high input slew rates
8. Protection functions are not designed for continuous repetitive operation and are considered outside normal operating range

TYPICAL CHARACTERISTIC CURVES

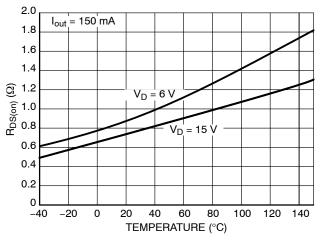


Figure 3. R_{DS(on)} vs. Temperature

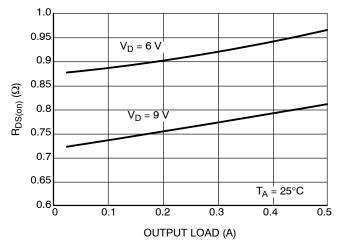


Figure 4. R_{DS(on)} vs. Output Load

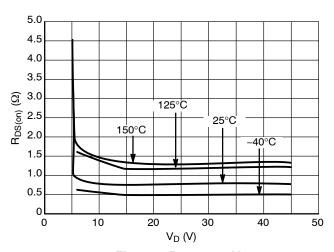


Figure 5. R_{DS(on)} vs. V_D

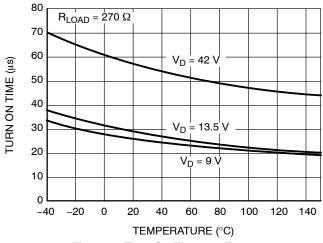


Figure 6. Turn On Time vs. Temperature

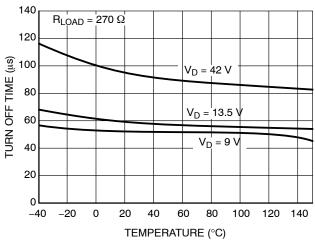


Figure 7. Turn Off Time vs. Temperature

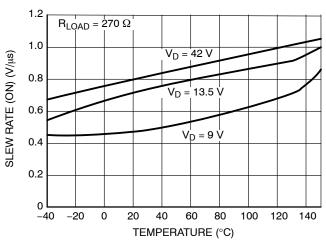


Figure 8. Slew Rate (ON) vs. Temperature

TYPICAL CHARACTERISTIC CURVES

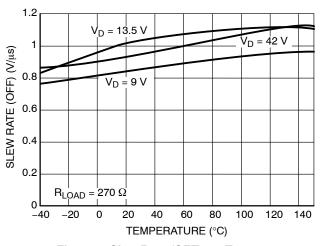


Figure 9. Slew Rate (OFF) vs. Temperature

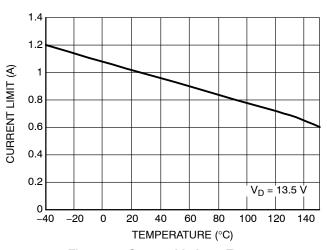


Figure 10. Current Limit vs. Temperature

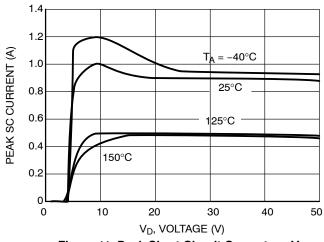


Figure 11. Peak Short Circuit Current vs. V_D Voltage

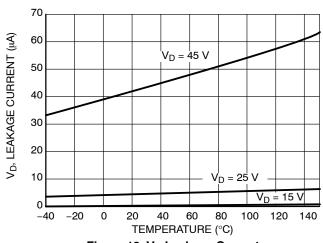


Figure 12. V_D Leakage Current vs. Temperature Off–State

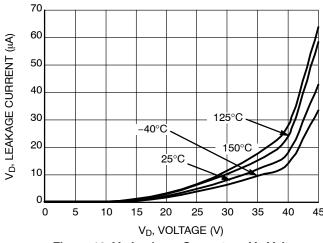


Figure 13. V_D Leakage Current vs. V_D Voltage Off-State

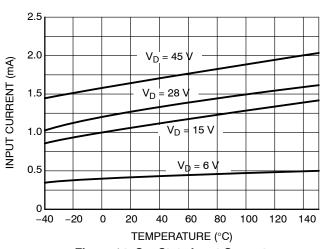


Figure 14. On-State Input Current vs.
Temperature

TYPICAL CHARACTERISTIC CURVES

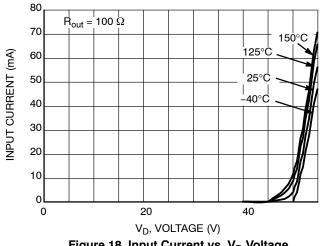


Figure 18. Input Current vs. V_D Voltage Off-State

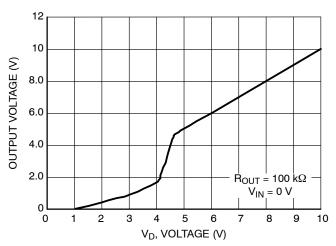


Figure 15. Output Voltage vs. V_D Voltage

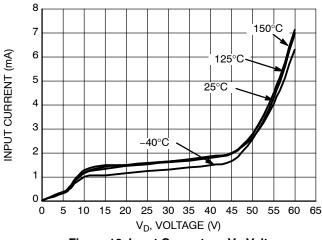


Figure 16. Input Current vs. V_D Voltage On–State

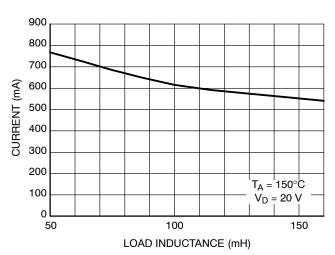


Figure 17. Single Pulse Maximum Switch-off Current vs. Load Inductance

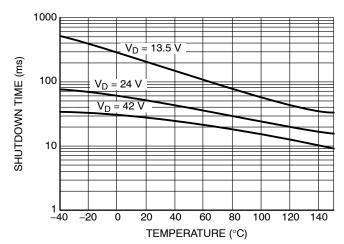


Figure 19. Initial Short-Circuit Shutdown Time vs. Temperature

TYPICAL CHARACTERISTIC CURVES

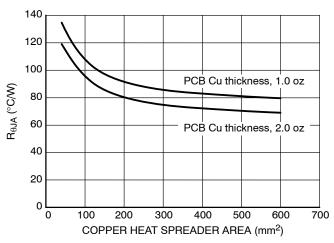


Figure 20. $R_{\theta JA}$ vs. Copper Area

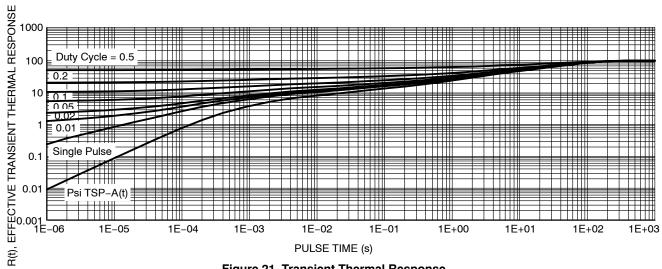


Figure 21. Transient Thermal Response

ISO PULSE TEST RESULTS

Test Pulse	Test Level	Test Results	Pulse Cycle Time and Generator Impedance
1	200 V	С	500 ms, 10 Ω
2	150 V	С	500 ms, 10 Ω
3a	200 V	С	100 ms, 50 Ω
3b	200 V	С	100 ms, 50 Ω
5	175 V	E(100 V)	400 ms, 2 Ω

ORDERING INFORMATION

Device	Package	Shipping [†]
NCV8450STT3G	SOT-223 (Pb-Free)	4000 / Tape & Reel
NCV8450ASTT3G	SOT-223 (Pb-Free)	4000 / Tape & Reel

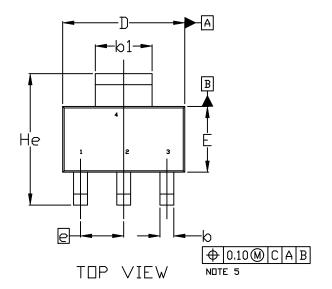
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

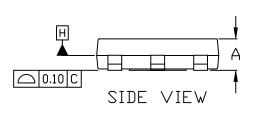


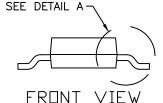


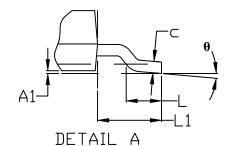
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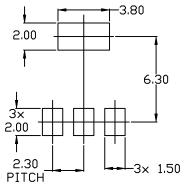




NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
 MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
- 4. DATUMS A AND B ARE DETERMINED AT DATUM H.
- 5. AI IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
- 6. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS 6 AND 61.

	MILLIMETERS			
DIM	MIN.	N□M.	MAX.	
Α	1.50	1.63	1.75	
A1	0.02	0.06	0.10	
Ø	0.60	0.75	0.89	
b1	2.90	3.06	3.20	
U	0.24	0.29	0.35	
D	6.30	6.50	6.70	
Е	3.30	3.50	3.70	
е		2,30 BSC	,	
L	0.20			
L1	1.50	1.75	2.00	
He	6.70	7.00	7.30	
θ	0°		10°	



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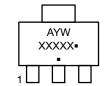
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DATE 02 OCT 2018

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 2: PIN 1. ANODE 2. CATHODE 3. NC 4. CATHODE	STYLE 3: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN	STYLE 4: PIN 1. SOURCE 2. DRAIN 3. GATE 4. DRAIN	STYLE 5: PIN 1. DRAIN 2. GATE 3. SOURCE 4. GATE
STYLE 6: PIN 1. RETURN 2. INPUT 3. OUTPUT 4. INPUT	STYLE 7: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 4. CATHODE	STYLE 8: CANCELLED	STYLE 9: PIN 1. INPUT 2. GROUND 3. LOGIC 4. GROUND	STYLE 10: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE
STYLE 11: PIN 1. MT 1 2. MT 2 3. GATE 4. MT 2	STYLE 12: PIN 1. INPUT 2. OUTPUT 3. NC 4. OUTPUT	STYLE 13: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR		

GENERIC MARKING DIAGRAM*



A = Assembly Location

Y = Year W = Work Week

XXXXX = Specific Device Code

= Pb-Free Package

(Note: Microdot may be in either location) *This information is generic. Please refer to

device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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